1 Scope

The present specifications shall apply to a RH1C.

2 Outline

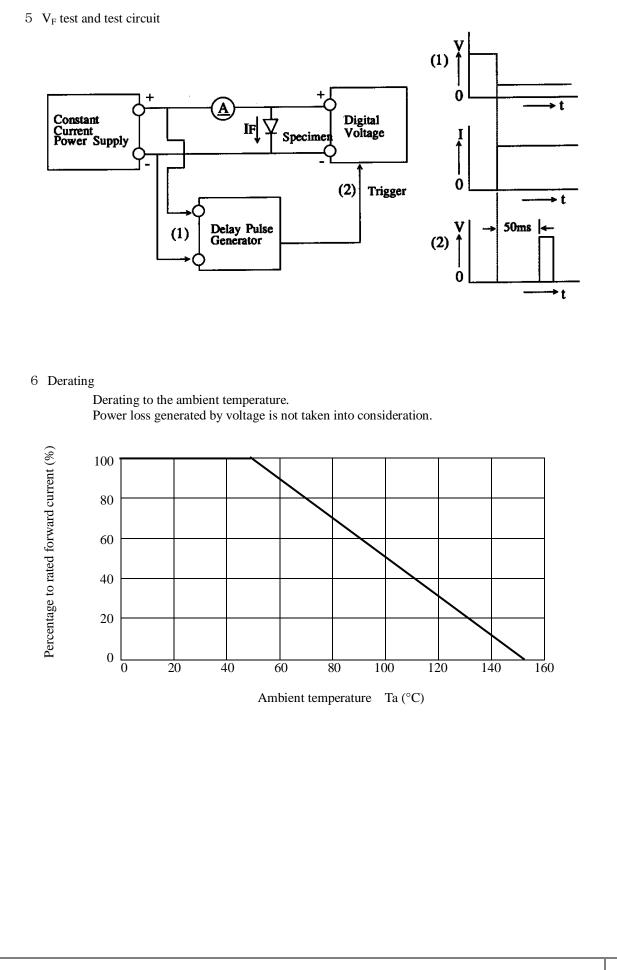
Туре	Silicon Diode			
Structure	Resin Molded Flammability:UL94-V0(Equivalent)			
Applications	High Frequency Rectification, etc.			

3 Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1 Transient Peak Reverse Voltage		V _{RSM}	V	1000	
2	2 Peak Reverse Voltage		V	1000	
3	Average Forward Current	$I_{F(AV)}$	А	0.6	Refer to derating curve in Section 6
4	Peak Surge Forward Current	I _{FSM}	А	35	10ms. Half sine wave, one shot
5	I ² t Limiting Value	I ² t	A ² s	6.125	$1 \text{ ms} \leq t \leq 10 \text{ ms}$
6	Junction Temperature	T_j	°C	-40 to +150	
7	Storage Temperature	T _{stg}	°C	-40 to +150	

4 Electrical characteristics (Ta= 25° C , unless otherwise specified)

No.	Io. Item		Unit	Value	Conditions
1	1 Forward Voltage Drop		V	1.3 max.	I _F =0.6A
2	2 Reverse Leakage Current		μΑ	5 max.	V _R =V _{RM}
3	3 Reverse Leakage Current Under High Temperature		μΑ	70 max.	$V_R = V_{RM}, T_a = 100^{\circ}C$
4 Reverse	Reverse Recovery Time	Trr-1	μs	4.0 max.	I _F =I _{RP} =10mA 90% Recovery point, T _j =25°C
	Reverse Recovery Time	Trr-2	μs	1.3 max.	$I_{F}=100mA, I_{R}=200mA$ 75% Recovery point $T_{j}=25^{\circ}C$
5	Thermal Resistance	Rth (j-l)	°C /W	15 max.	Between Junction and Lead



- 7Package information
 - 7-1 Package type, physical dimensions and material

